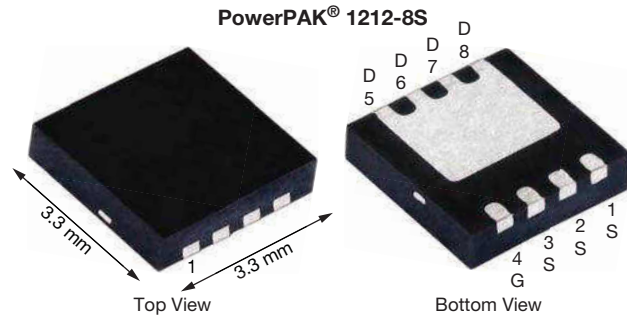


## N-Channel 25 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) (MAX.)	I <sub>D</sub> (A) <sup>a, g</sup>	Q <sub>g</sub> (TYP.)
25	0.00152 at V <sub>GS</sub> = 10 V	60	21.8 nC
	0.00224 at V <sub>GS</sub> = 4.5 V	60	


**Ordering Information:**

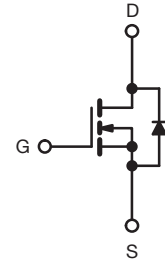
SiSS28DN-T1-GE3 (lead (Pb)-free and halogen-free)

**FEATURES**

- TrenchFET® Gen IV power MOSFET
- Optimized Q<sub>g</sub>, Q<sub>gd</sub>, and Q<sub>gd</sub>/Q<sub>gs</sub> ratio reduces switching related power loss
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**
**APPLICATIONS**

- Synchronous rectification
- High power density DC/DC
- VRMs and embedded DC/DC
- Synchronous buck converter
- Load switching
- Battery management



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	25	V
Gate-Source Voltage		V <sub>GS</sub>	+16, -12	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	60 <sup>g</sup>	A
	T <sub>C</sub> = 70 °C		60 <sup>g</sup>	
	T <sub>A</sub> = 25 °C		41.8 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C		33.1 <sup>b, c</sup>	
Pulsed Drain Current (t = 100 μs)		I <sub>DM</sub>	150	A
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	41.8	
	T <sub>A</sub> = 25 °C		4.3 <sup>b, c</sup>	
Single Pulse Avalanche Current		L = 0.1 mH	I <sub>AS</sub>	30
Single Pulse Avalanche Energy			E <sub>AS</sub>	45
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	57	W
	T <sub>C</sub> = 70 °C		36	
	T <sub>A</sub> = 25 °C		4.8 <sup>b, c</sup>	
	T <sub>A</sub> = 70 °C		3 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering Recommendations (Peak temperature) <sup>d, e</sup>			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 10 s	R <sub>thJA</sub>	21	26	°C/W
Maximum Junction-to-Case (Drain)	Steady state	R <sub>thJC</sub>	1.7	2.2	

**Notes**

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 70 °C/W.
- Package limited.



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	25	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 10 mA	-	19	-	mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	-4.2	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1	-	2	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +16 V, -12 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V = 25 V, V <sub>DS GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	-	0.00115	0.00152	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	0.00160	0.00224	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 15 A	-	95	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	3640	-	pF
Output Capacitance	C <sub>oss</sub>		-	1155	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	200	-	
C <sub>rss</sub> /C <sub>iss</sub> Ratio			-	0.043	0.085	
Total Gate Charge	Q <sub>g</sub>	V = 10 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	-	48.1	75	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	21.8	35	
Gate-Drain Charge	Q <sub>gd</sub>		-	8.6	-	
Output Charge	Q <sub>oss</sub>		-	3.4	-	
Output Charge	Q <sub>oss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V	-	17.5	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.2	0.7	1.4	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 1 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	11	22	ns
Rise Time	t <sub>r</sub>		-	18	36	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	30	60	
Fall Time	t <sub>f</sub>		-	8	16	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 1 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	23	46	
Rise Time	t <sub>r</sub>		-	27	54	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	28	56	
Fall Time	t <sub>f</sub>		-	10	20	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	48.1	A
Pulse Diode Forward Current (t = 100 μs)	I <sub>SM</sub>		-	-	150	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A	-	0.73	1.1	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	36	72	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	29	58	nC
Reverse Recovery Fall Time	t <sub>a</sub>		-	16	-	ns
Reverse Recovery Rise Time	t <sub>b</sub>		-	20	-	

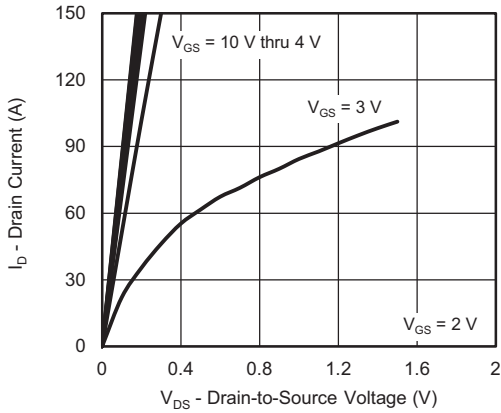
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

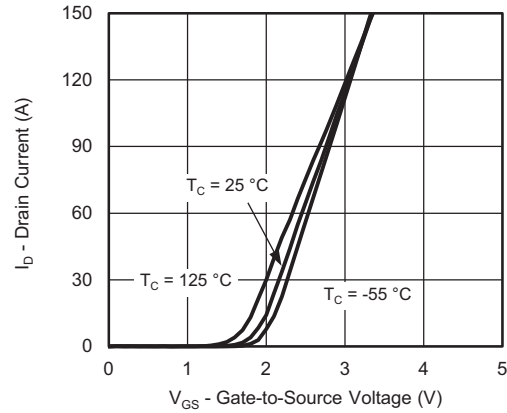
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



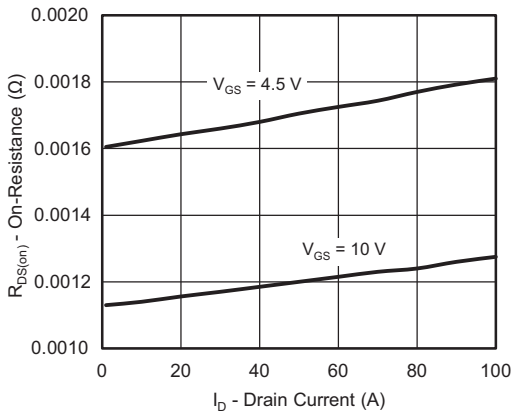
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



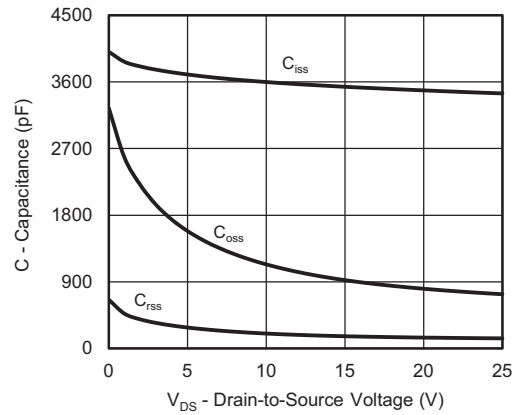
Output Characteristics



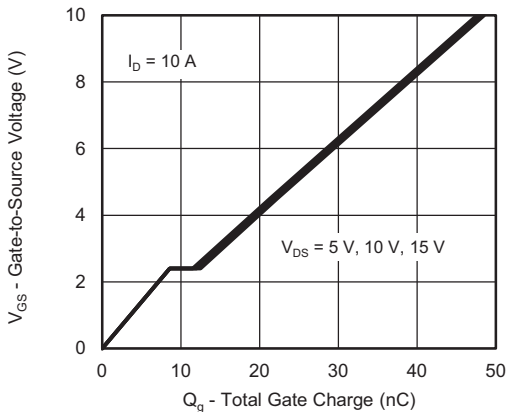
Transfer Characteristics



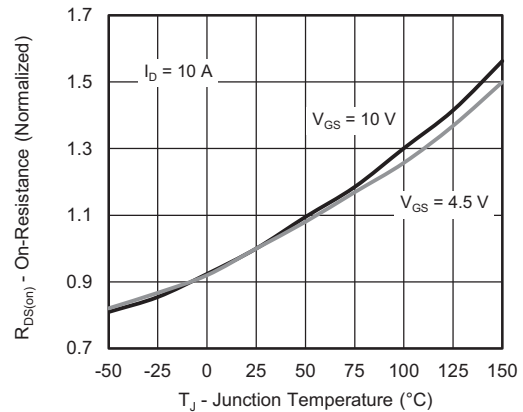
On-Resistance vs. Drain Current



Capacitance



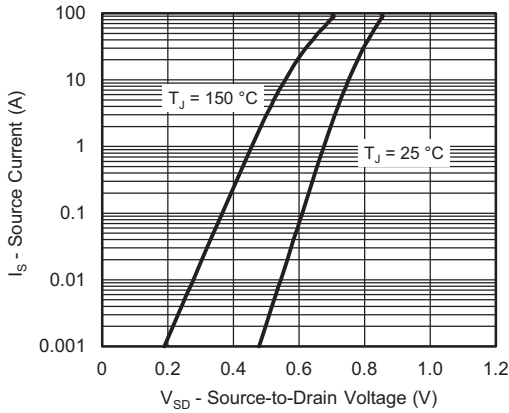
Gate Charge



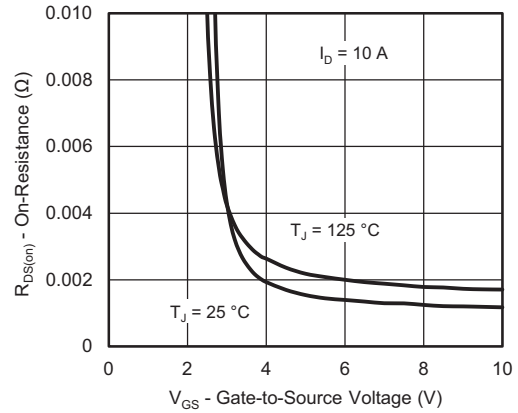
On-Resistance vs. Junction Temperature



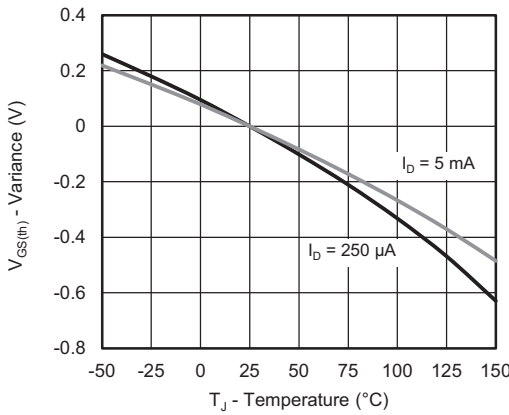
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



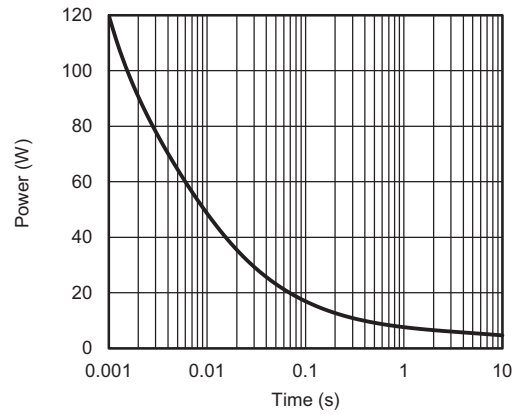
Source-Drain Diode Forward Voltage



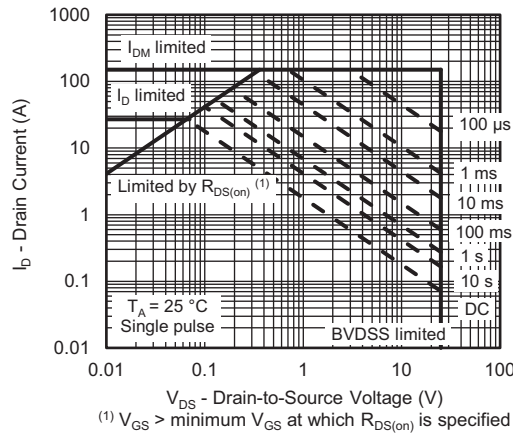
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

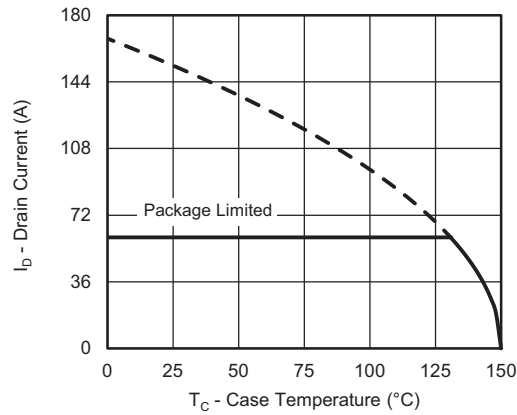
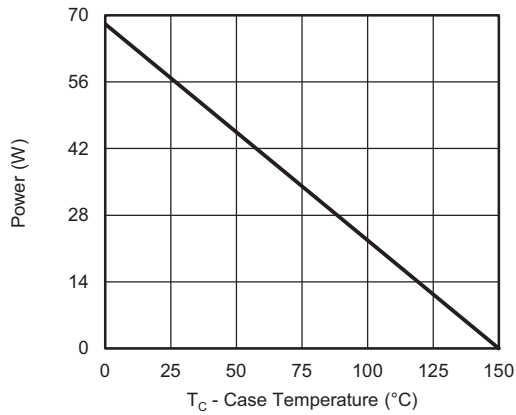
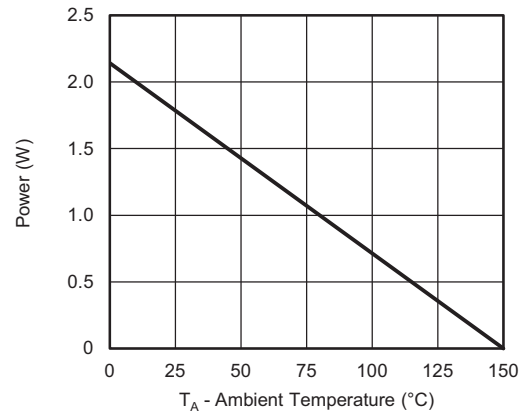


Single Pulse Power, Junction-to-Ambient



(1)  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

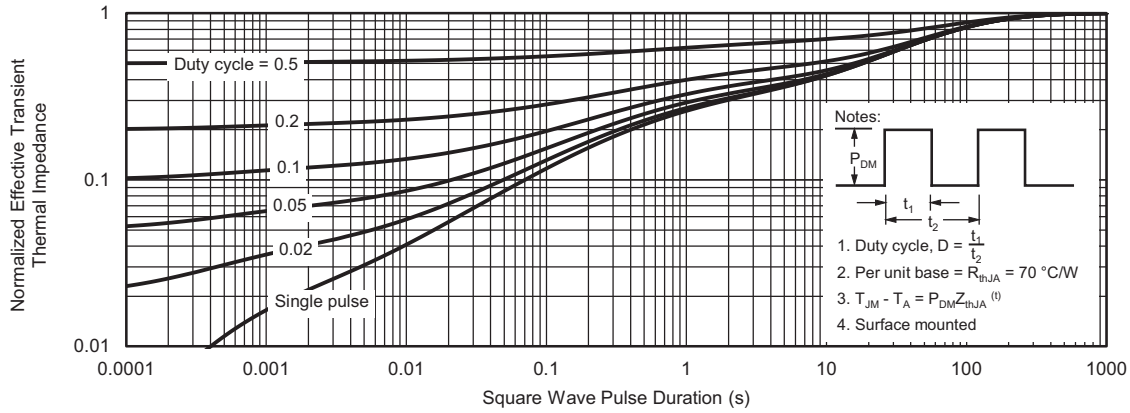
Safe Operating Area

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating <sup>a</sup>**

**Power, Junction-to-Case**

**Power, Junction-to-Ambient**
**Note**

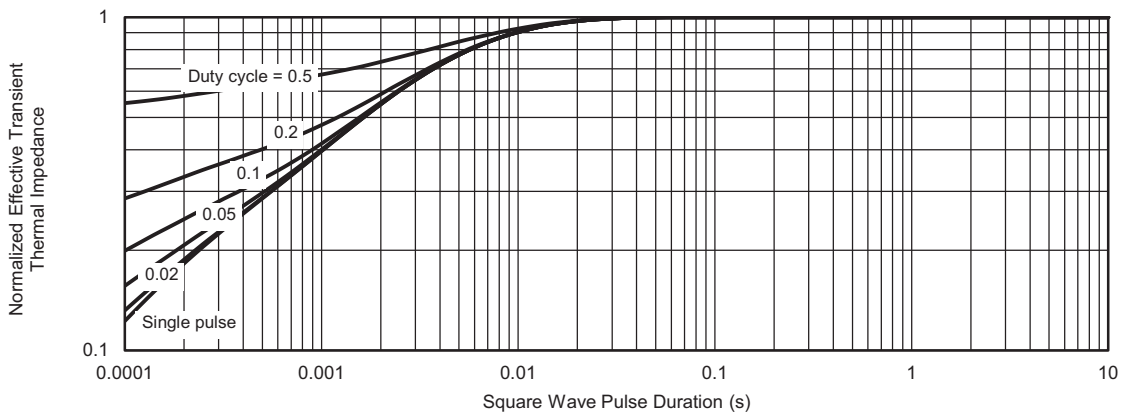
- a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?76552](http://www.vishay.com/ppg?76552).

**Case Outline for PowerPAK® 1212-8S**


DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.67	0.75	0.83	0.026	0.030	0.033
A1	0.00	-	0.05	0.000	-	0.002
A3	0.20 ref.			0.008 ref		
b	0.25	0.30	0.35	0.010	0.012	0.014
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.15	2.25	2.35	0.085	0.089	0.093
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	1.60	1.70	1.80	0.063	0.067	0.071
e	0.65 bsc.			0.026 bsc.		
K	0.76 ref.			0.030 ref.		
K1	0.41 ref.			0.016 ref.		
L	0.33	0.43	0.53	0.013	0.017	0.021
Z	0.525 ref.			0.021 ref.		

ECN: C20-0862-Rev. B, 20-Jul-2020  
DWG: 6008

## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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